



STB60NF06

N-CHANNEL 60V - 0.014Ω - 60A D2PAK

STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB60NF06	60V	< 0.016 Ω	60A

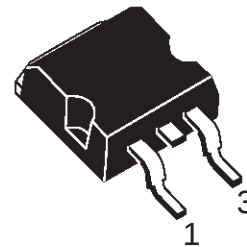
- TYPICAL R_{DS(on)} = 0.014Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL

DESCRIPTION

This Power Mosfet series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

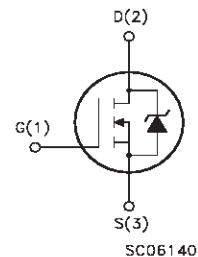
APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL
- AUTOMOTIVE



D2PAK

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	60	A
I _D	Drain Current (continuous) at T _C = 100°C	42	A
I _{DM} (●)	Drain Current (pulsed)	240	A
P _{TOT}	Total Dissipation at T _C = 25°C	110	W
	Derating Factor	0.67	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	4	V/ns
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 60A, di/dt ≤ 400 A/μs, V_{DD} ≤ 24V, T_j ≤ T_{jMAX}

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
Rthj-sink	Thermal Resistance case-sink Max	0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	30	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 30 V)	360	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 30 A		0.014	0.016	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} = 15V, I _D = 30 A		20		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1810		pF
C _{oss}	Output Capacitance			360		pF
C _{rss}	Reverse Transfer Capacitance			125		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30\text{ V}$, $I_D = 30\text{ A}$		16		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		108		ns
Q_g	Total Gate Charge	$V_{DD} = 48\text{ V}$, $I_D = 60\text{ A}$, $V_{GS} = 10\text{ V}$		49	66	nC
Q_{gs}	Gate-Source Charge			18		nC
Q_{gd}	Gate-Drain Charge			14		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 30\text{ V}$, $I_D = 30\text{ A}$		43		ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		20		ns
$t_{d(off)}$	Off-voltage Rise Time	$V_{clamp} = 48\text{ V}$, $I_D = 60\text{ A}$		40		ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$		12		ns
t_c	Cross-over Time	(see test circuit, Figure 3)		21		ns

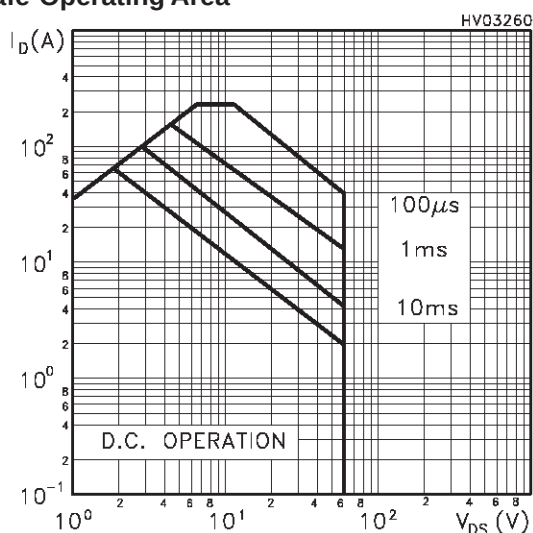
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				60	A
$I_{SDM(1)}$	Source-drain Current (pulsed)				240	A
$V_{SD(2)}$	Forward On Voltage	$I_{SD} = 60\text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 60\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		73		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 25\text{ V}$, $T_J = 150^\circ\text{C}$		182		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		5		A

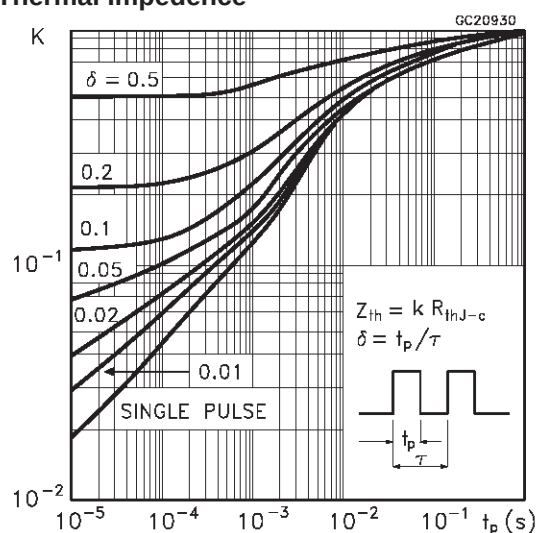
Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2. Pulse width limited by safe operating area.

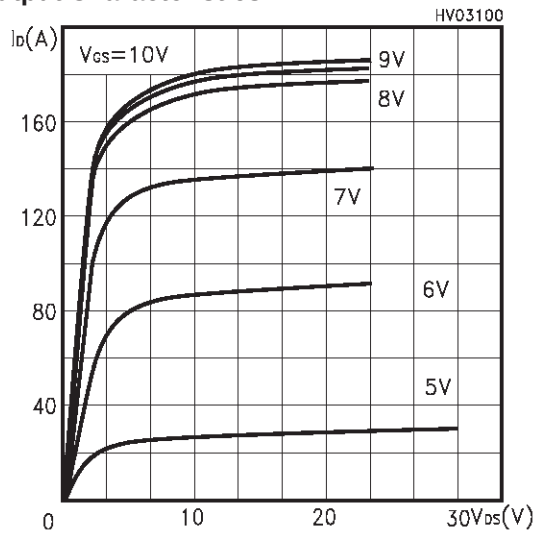
Safe Operating Area



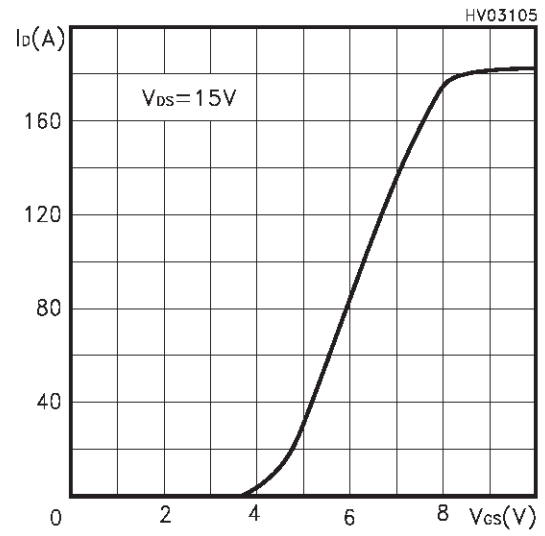
Thermal Impedance



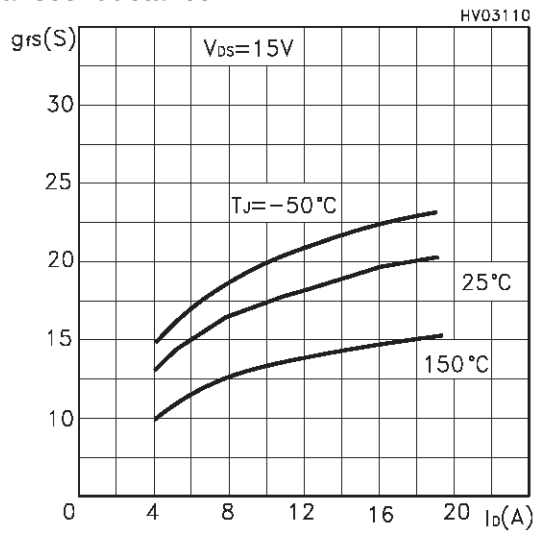
Output Characteristics



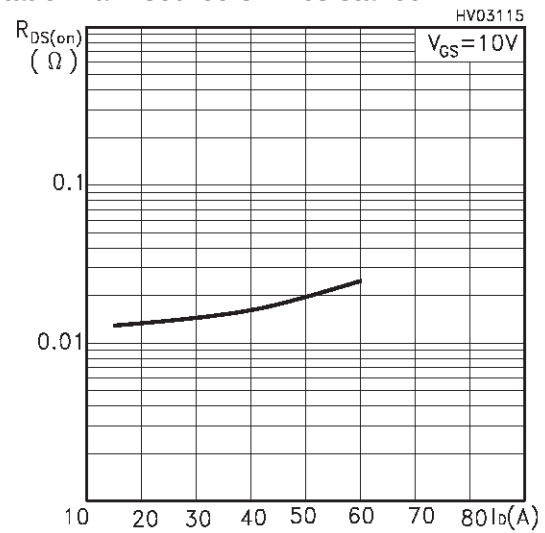
Transfer Characteristics



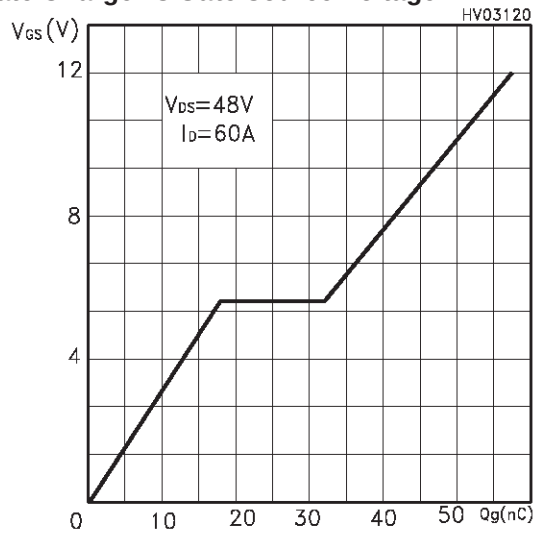
Transconductance



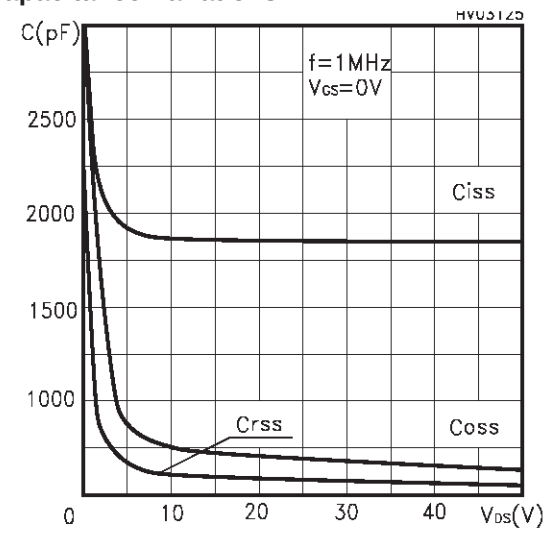
Static Drain-source On Resistance



Gate Charge vs Gate-source Voltage



Capacitance Variations



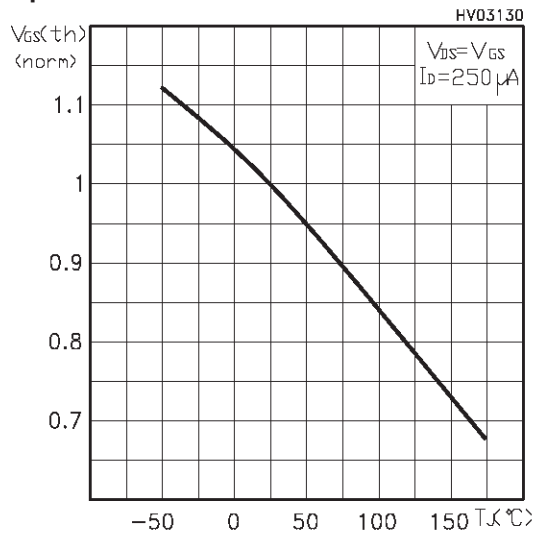
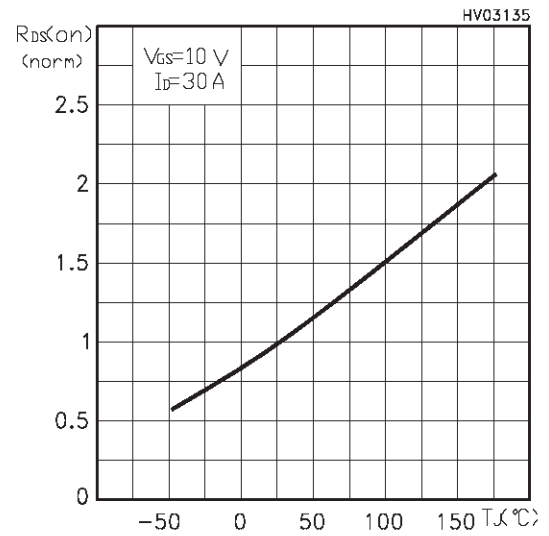
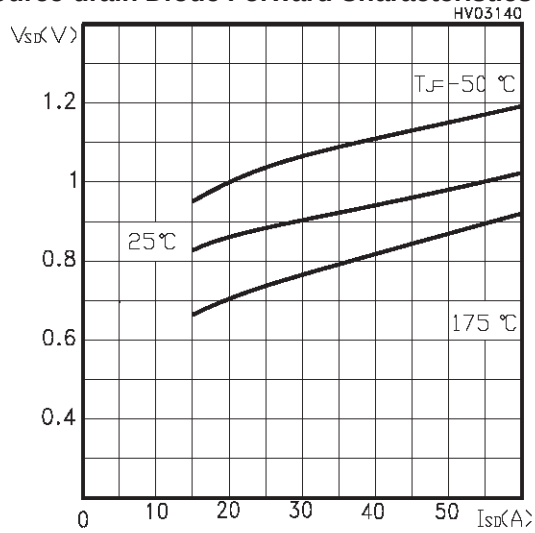
Normalized Gate Threshold Voltage vs Temperature**Normalized On Resistance vs Temperature****Source-drain Diode Forward Characteristics**

Fig. 1: Unclamped Inductive Load Test Circuit

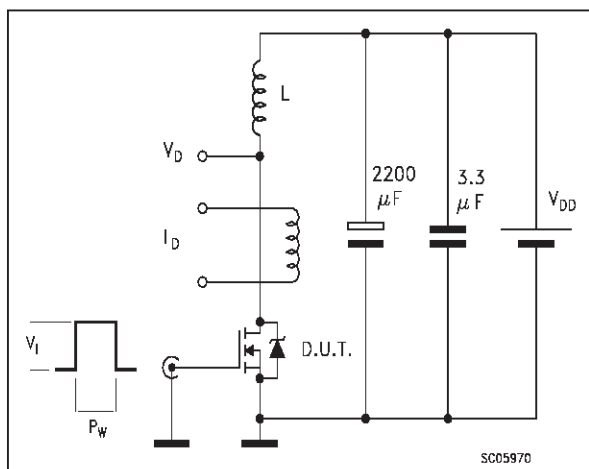


Fig. 2: Unclamped Inductive Waveform

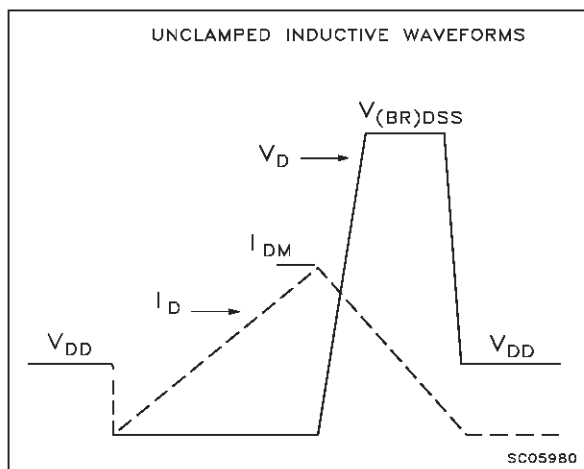


Fig. 3: Switching Times Test Circuit For Resistive Load

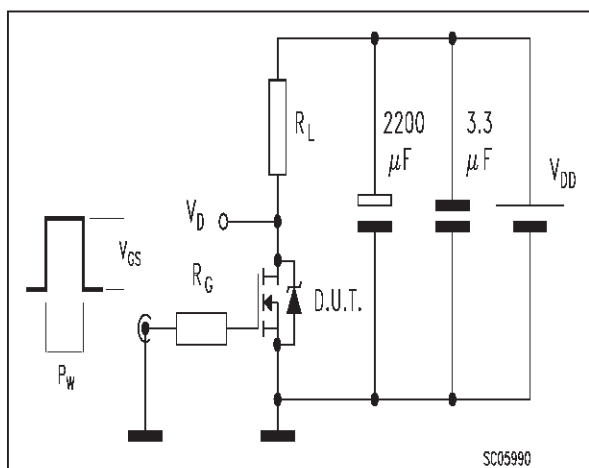


Fig. 4: Gate Charge test Circuit

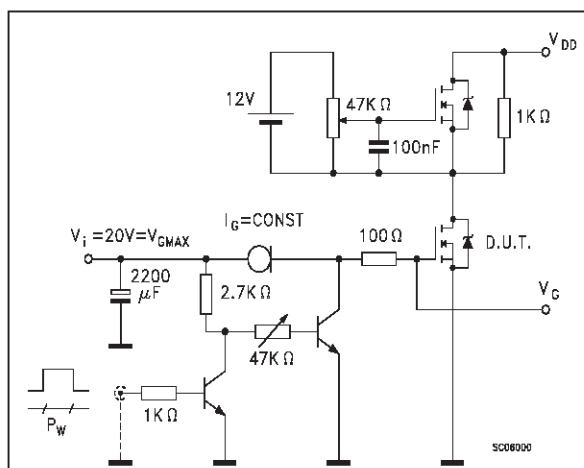
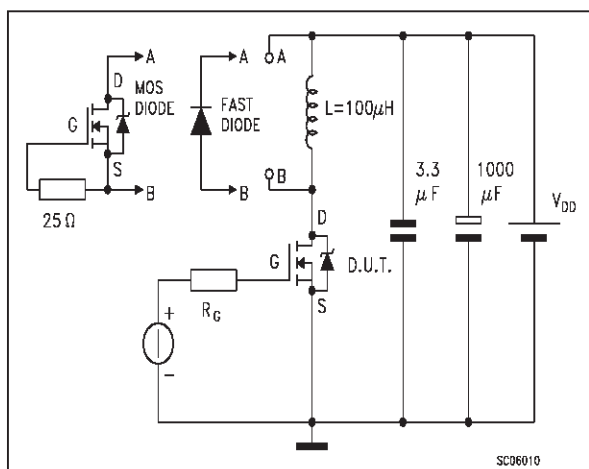
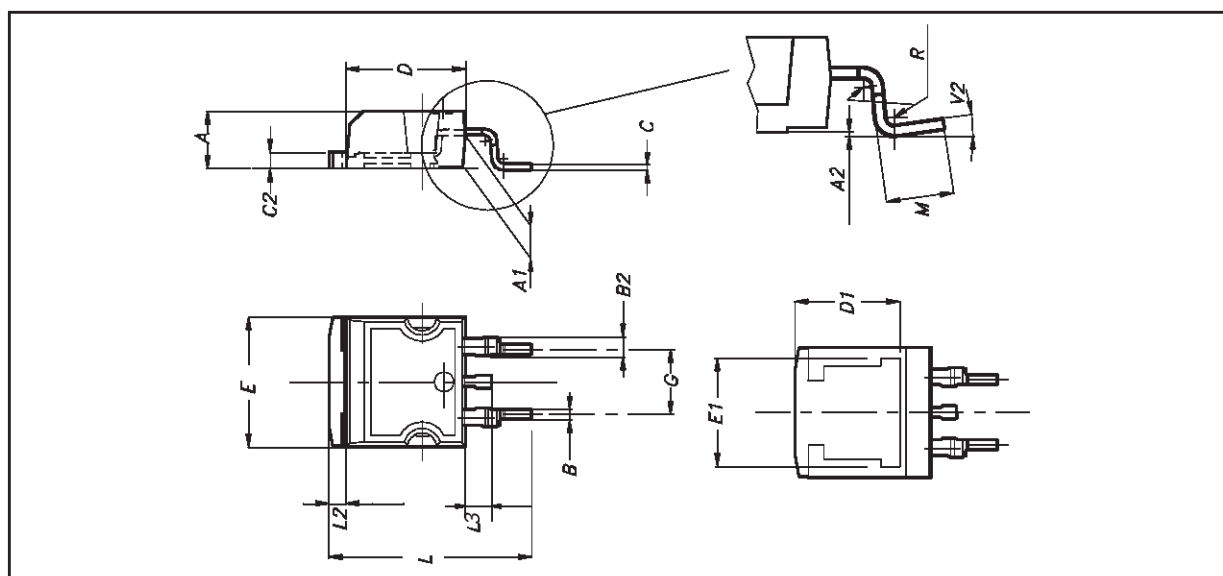


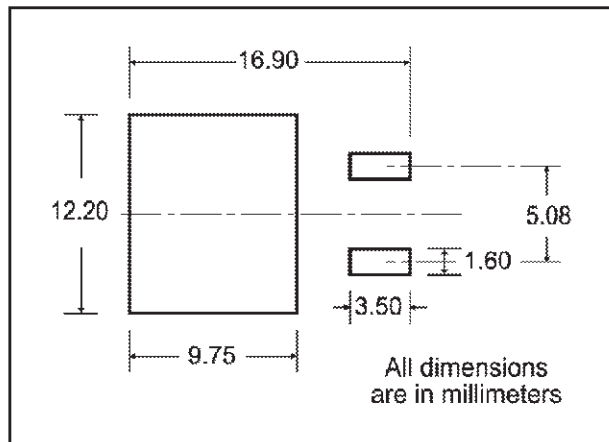
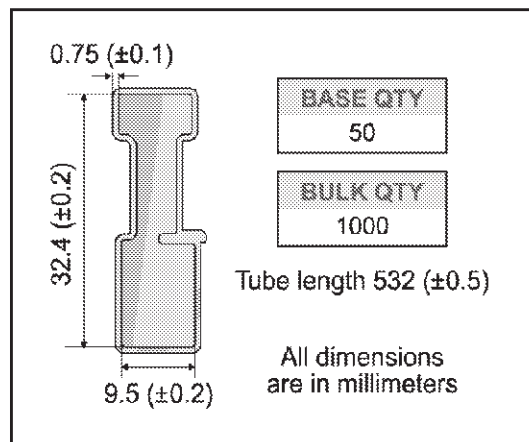
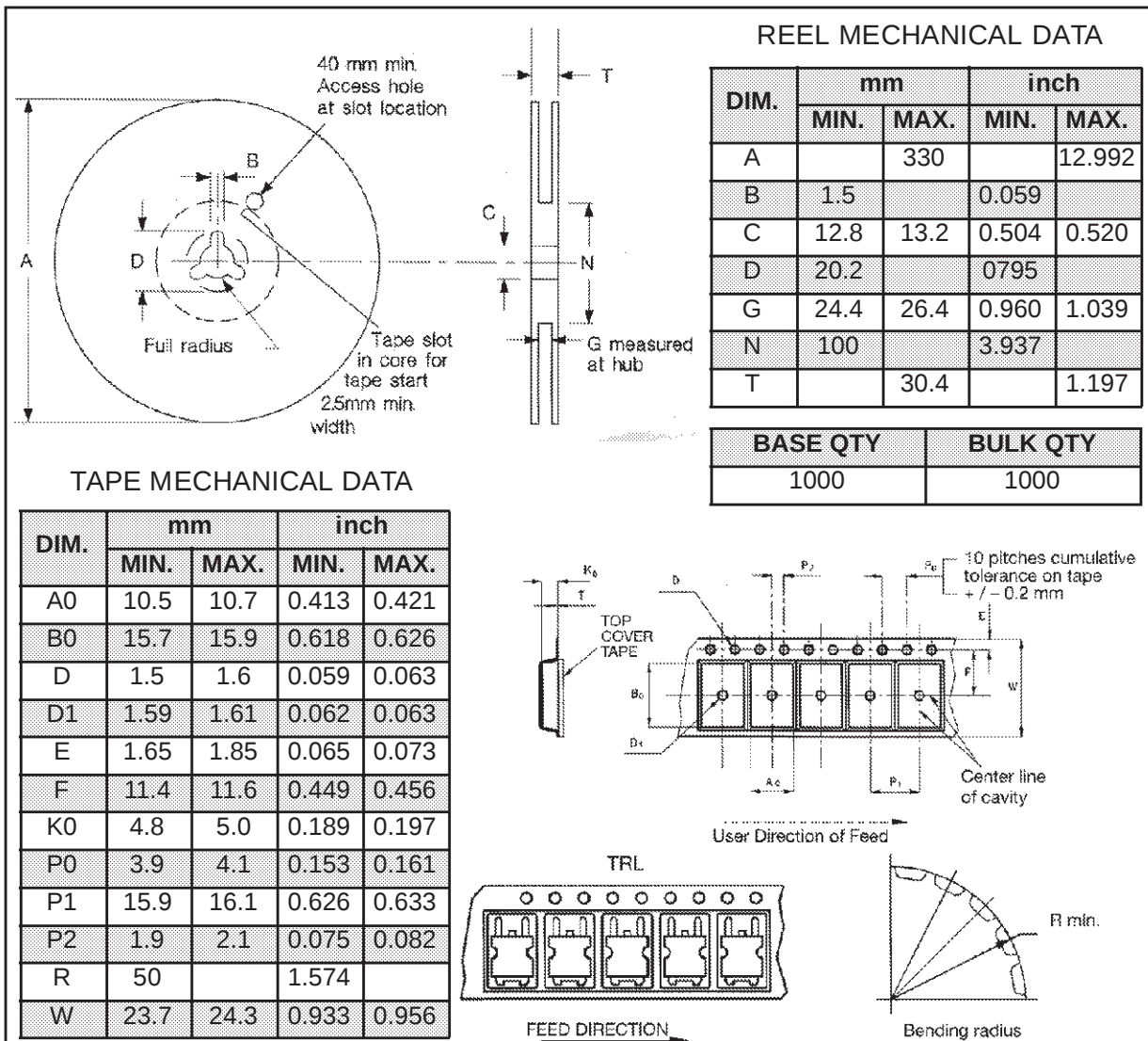
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



D²PAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")***

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